ONIUM-CONTAINING CMP COMPOSITIONS AND METHODS OF USE THEREOF

ABSTRACT

The present invention provides a chemical-mechanical polishing (CMP) composition suitable for polishing semiconductor materials. The composition has a pH of 5 or less and comprises colloidal silica, at least one onium compound selected from the group consisting of a phosphonium salt, a sulfonium salt, and a combination thereof, and an aqueous carrier therefor; A CMP method for polishing a surface of a semiconductor material utilizing the composition is also disclosed.

Figure 1